



# FDMS7600AS

## Dual N-Channel PowerTrench<sup>®</sup> MOSFET

N-Channel: 30 V, 30 A, 7.5 mΩ N-Channel: 30 V, 40 A, 2.8 mΩ

### Features

Q1: N-Channel

- Max  $r_{DS(on)}$  = 7.5 mΩ at  $V_{GS} = 10$  V,  $I_D = 12$  A
- Max  $r_{DS(on)}$  = 12 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 10$  A

Q2: N-Channel

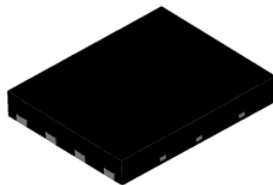
- Max  $r_{DS(on)}$  = 2.8 mΩ at  $V_{GS} = 10$  V,  $I_D = 20$  A
- Max  $r_{DS(on)}$  = 3.3 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 18$  A
- RoHS Compliant

### General Description

This device includes two specialized N-Channel MOSFETs in a dual MLP package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET<sup>™</sup> (Q2) have been designed to provide optimal power efficiency.

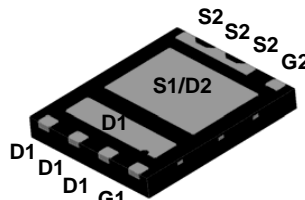
### Applications

- Computing
- Communications
- General Purpose Point of Load
- Notebook  $V_{CORE}$

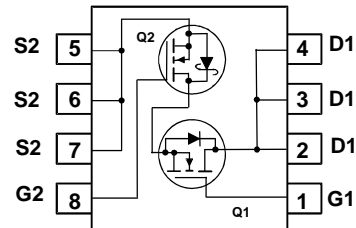


Top

Power 56



Bottom



### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
$V_{DS}$	Drain to Source Voltage	30	30	V
$V_{GS}$	Gate to Source Voltage (Note 3)	$\pm 20$	$\pm 20$	V
$I_D$	Drain Current -Continuous $T_C = 25$ °C	30	40	A
	-Continuous $T_A = 25$ °C	12 <sup>1a</sup>	22 <sup>1b</sup>	
	-Pulsed	40	60	
$P_D$	Power Dissipation for Single Operation $T_A = 25$ °C	2.2 <sup>1a</sup>	2.5 <sup>1b</sup>	W
	$T_A = 25$ °C	1.0 <sup>1c</sup>	1.0 <sup>1d</sup>	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150		°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	57 <sup>1a</sup>	50 <sup>1b</sup>	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125 <sup>1c</sup>	120 <sup>1d</sup>	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	2	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS7600AS	FDMS7600AS	Power 56	13 "	12 mm	3000 units

**Electrical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$ $I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$ $I_D = 1\text{ mA}$ , referenced to $25\text{ }^\circ\text{C}$	Q1 Q2		15 18		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$	Q1 Q2			1 500	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$	Q1 Q2			100 100	nA nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$ $V_{GS} = V_{DS}$ , $I_D = 1\text{ mA}$	Q1 Q2	1 1	1.8 1.5	3 3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$ $I_D = 1\text{ mA}$ , referenced to $25\text{ }^\circ\text{C}$	Q1 Q2		-6 -5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 12\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 12\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	Q1		6.0 8.5 8.3	7.5 12 12	m $\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 18\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	Q2		2.2 2.6 2.6	2.8 3.3 3.8	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 12\text{ A}$ $V_{DS} = 5\text{ V}$ , $I_D = 20\text{ A}$	Q1 Q2		63 190		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	Q1: $V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	Q1 Q2		1315 5265	1750 7005	pF
$C_{oss}$	Output Capacitance	Q2: $V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	Q1 Q2		445 2150	600 2860	pF
$C_{riss}$	Reverse Transfer Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	Q1 Q2		45 200	70 300	pF
$R_g$	Gate Resistance		Q1 Q2		0.9 0.3		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	Q1: $V_{DD} = 15\text{ V}$ , $I_D = 12\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		8.6 18	18 32	ns
$t_r$	Rise Time		Q1 Q2		2.5 7.6	10 16	ns
$t_{d(off)}$	Turn-Off Delay Time	Q2: $V_{DD} = 15\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		20 45	32 72	ns
$t_f$	Fall Time		Q1 Q2		2.3 5.2	10 10	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $10\text{ V}$	Q1 Q2		20 81	28 113	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $4.5\text{ V}$	Q1 Q2		9.3 37	13 52	nC
$Q_{gs}$	Gate to Source Gate Charge	Q2 $V_{DD} = 15\text{ V}$ , $I_D = 20\text{ A}$	Q1 Q2		4.3 13		nC
$Q_{gd}$	Gate to Drain "Miller" Charge		Q1 Q2		2.2 9.6		nC

### Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

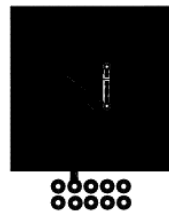
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
<b>Drain-Source Diode Characteristics</b>							
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 12\text{ A}$ (Note 2)	Q1		0.8	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$ (Note 2)	Q2		0.7	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 12\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1		27	43	ns
			Q2		47	75	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 20\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$	Q1		10	18	nC
			Q2		80	128	

**Notes:**

1:  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 57 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 50 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



c. 125 °C/W when mounted on a minimum pad of 2 oz copper



d. 120 °C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3: As an N-ch device, the negative  $V_{GS}$  rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

**Typical Characteristics (Q1 N-Channel)**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

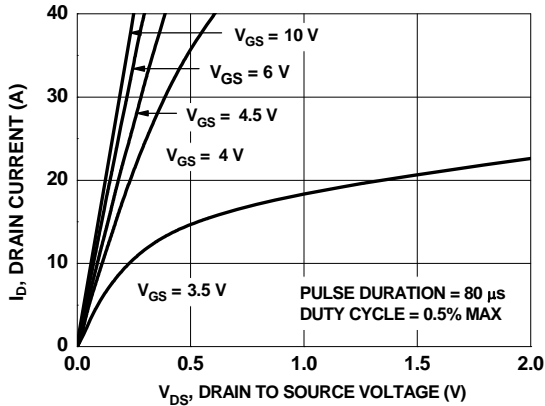


Figure 1. On Region Characteristics

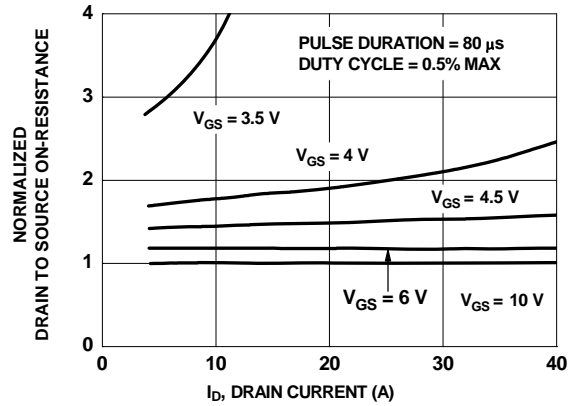


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

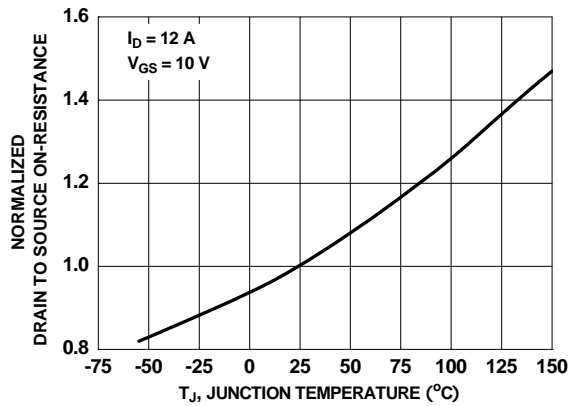


Figure 3. Normalized On Resistance vs Junction Temperature

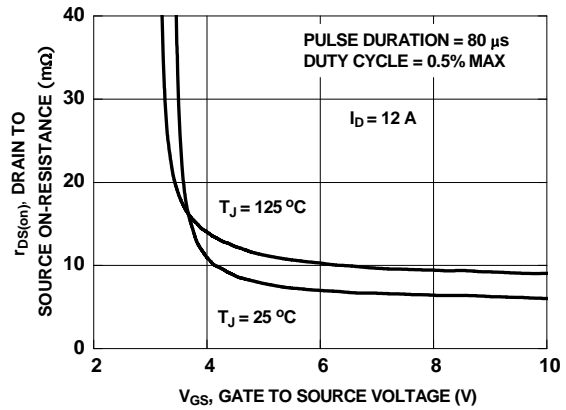


Figure 4. On-Resistance vs Gate to Source Voltage

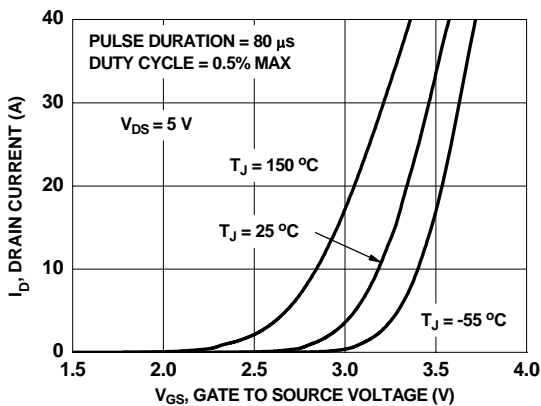


Figure 5. Transfer Characteristics

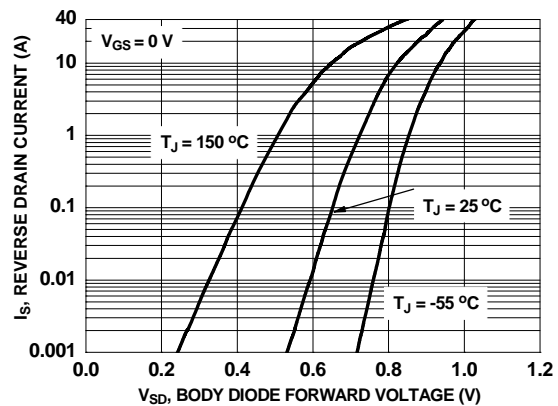
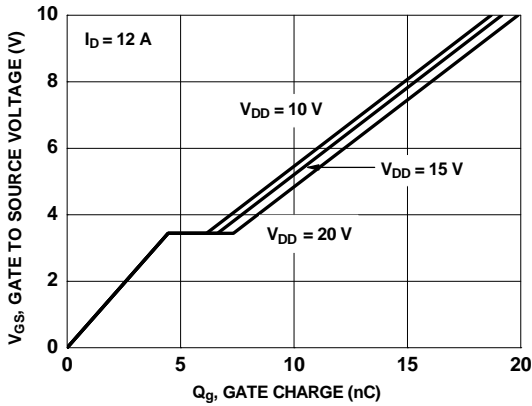
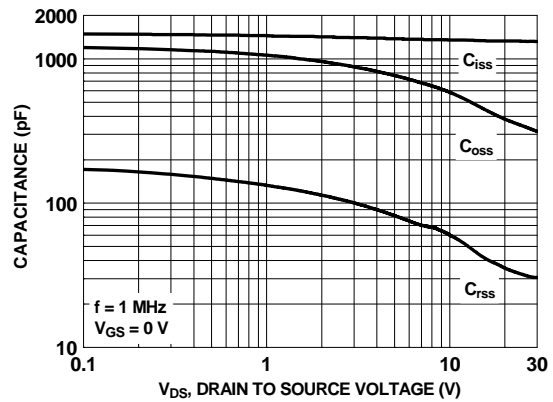


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

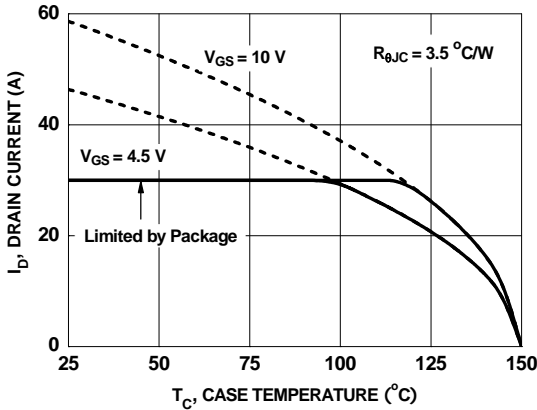
**Typical Characteristics (Q1 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted



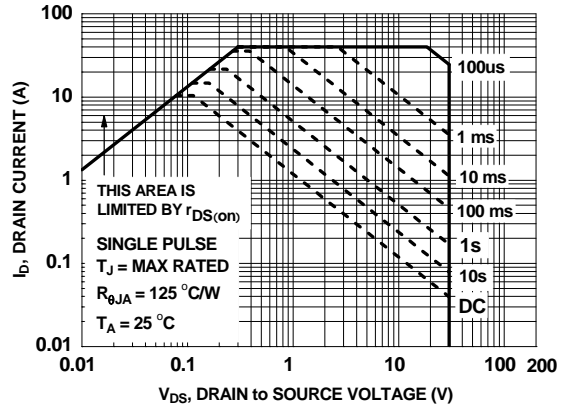
**Figure 7. Gate Charge Characteristics**



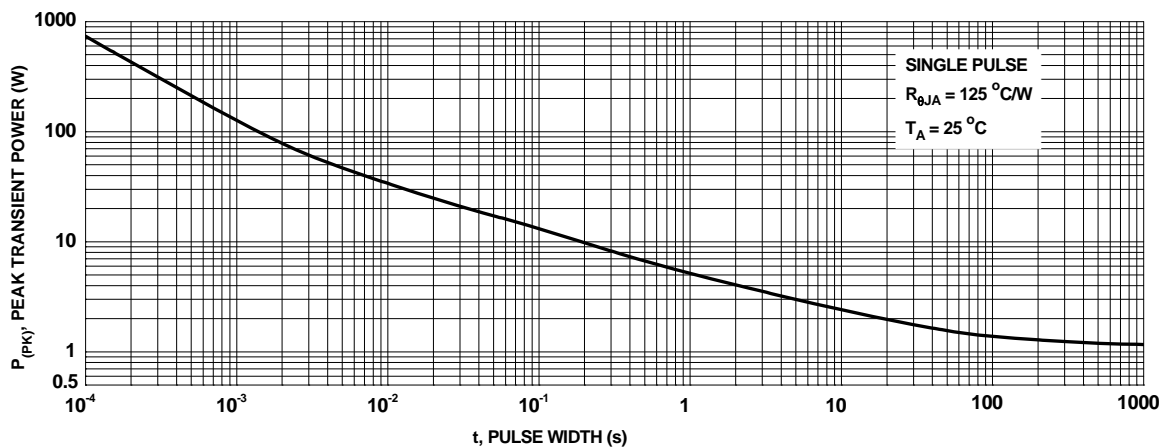
**Figure 8. Capacitance vs Drain to Source Voltage**



**Figure 9. Maximum Continuous Drain Current vs Case Temperature**

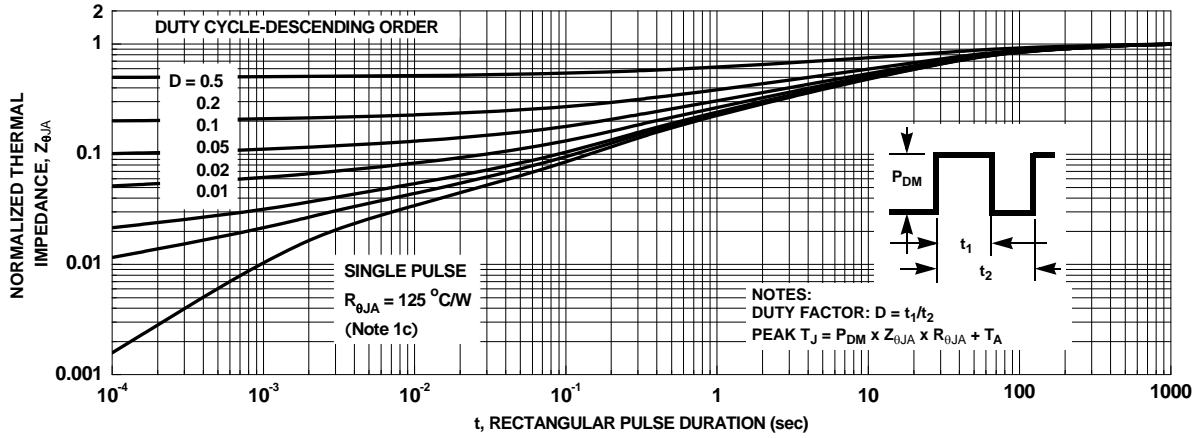


**Figure 10. Forward Bias Safe Operating Area**



**Figure 11. Single Pulse Maximum Power Dissipation**

**Typical Characteristics (Q1 N-Channel)**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure 12. Junction-to-Ambient Transient Thermal Response Curve**

**Typical Characteristics (Q2 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted

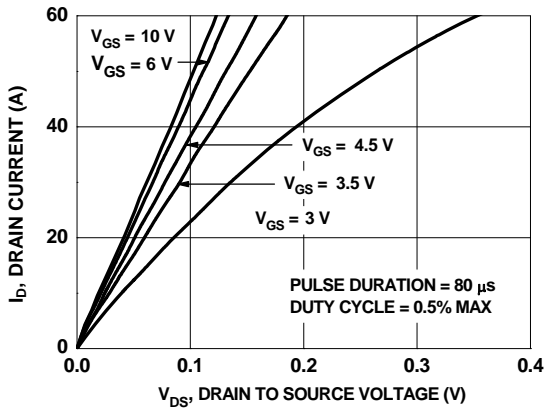


Figure 13. On-Region Characteristics

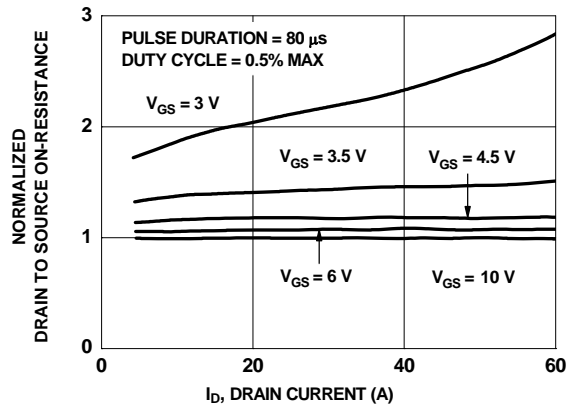


Figure 14. Normalized on-Resistance vs Drain Current and Gate Voltage

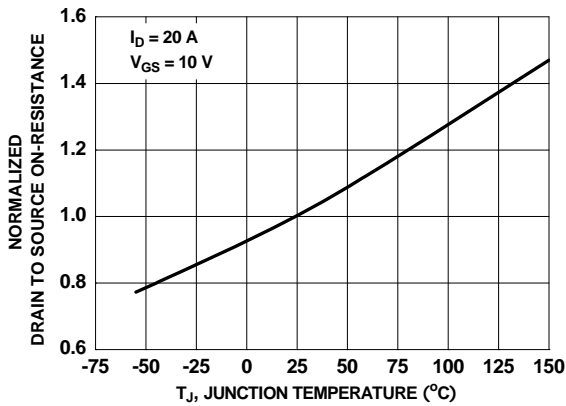


Figure 15. Normalized On-Resistance vs Junction Temperature

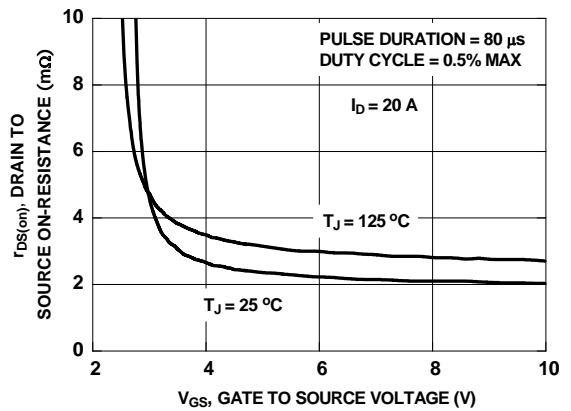


Figure 16. On-Resistance vs Gate to Source Voltage

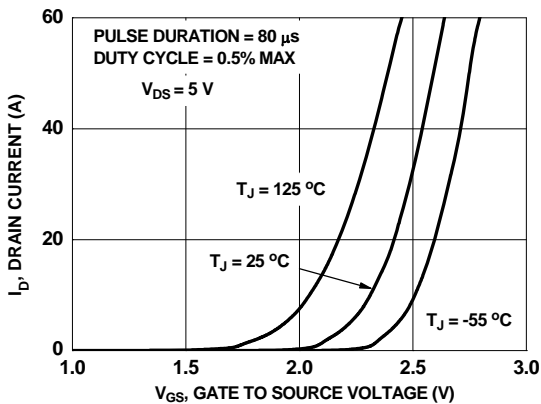


Figure 17. Transfer Characteristics

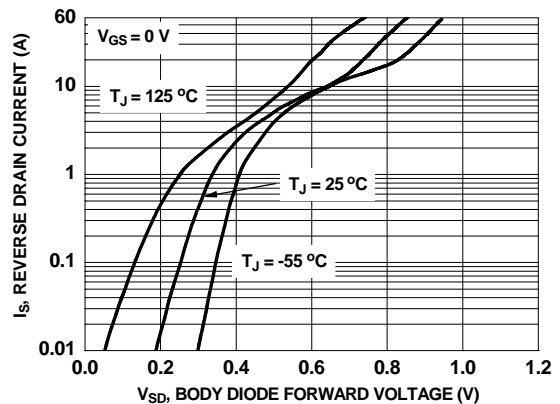
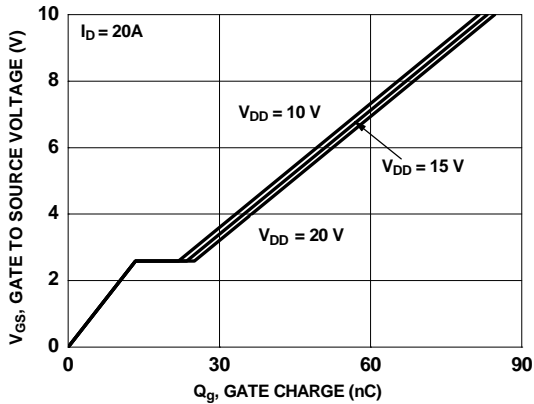
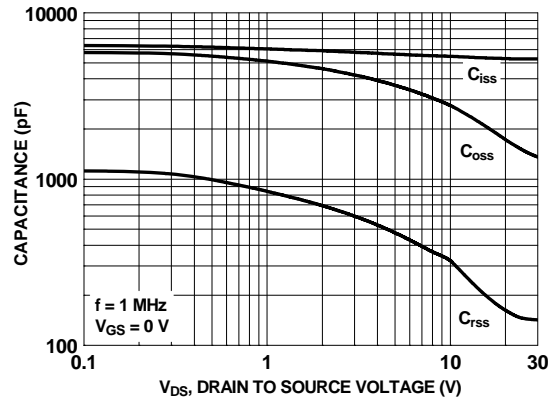


Figure 18. Source to Drain Diode Forward Voltage vs Source Current

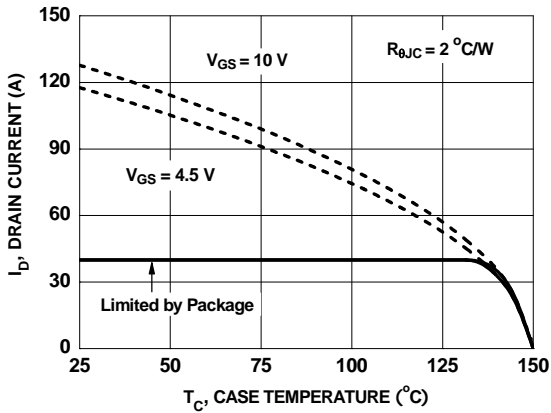
**Typical Characteristics (Q2 N-Channel)**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



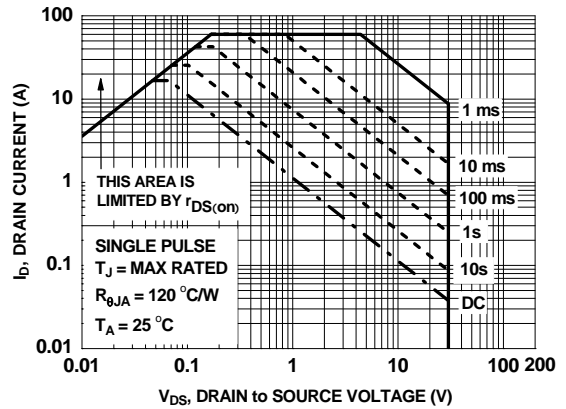
**Figure 19. Gate Charge Characteristics**



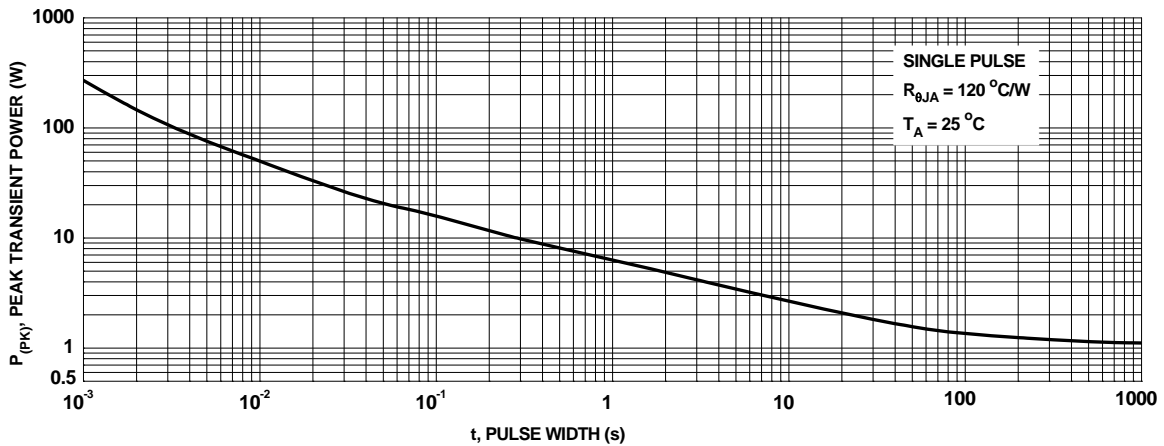
**Figure 20. Capacitance vs Drain to Source Voltage**



**Figure 21. Maximum Continuous Drain Current vs Case Temperature**



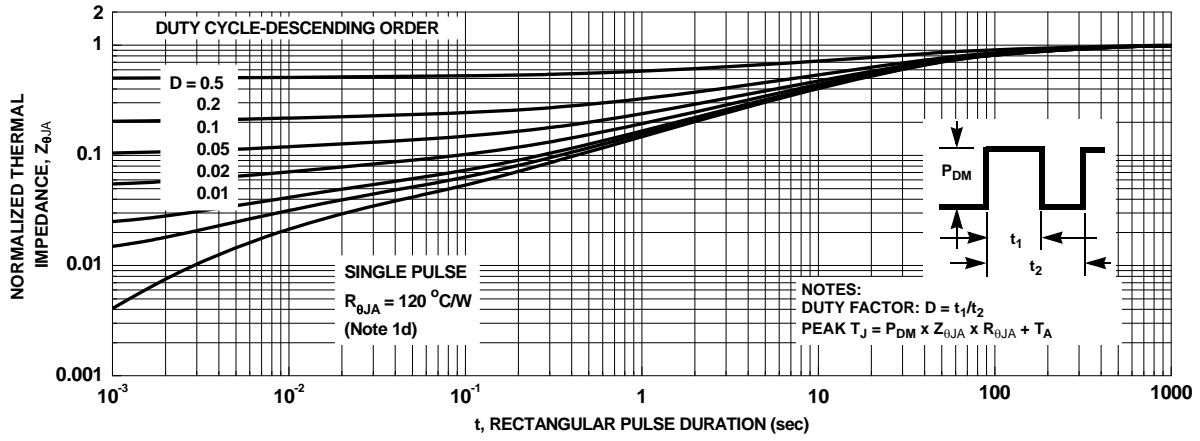
**Figure 22. Forward Bias Safe Operating Area**



**Figure 23. Single Pulse Maximum Power Dissipation**



**Typical Characteristics (Q2 N\_Channel)**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure24. Junction-to-Ambient Transient Thermal Response Curve**

## Typical Characteristics (continued)

### SyncFET<sup>™</sup> Schottky body diode Characteristics

Fairchild's SyncFET<sup>™</sup> process embeds a Schottky diode in parallel with PowerTrench<sup>®</sup> MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 25 shows the reverse recovery characteristic of the FDMS7600AS.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

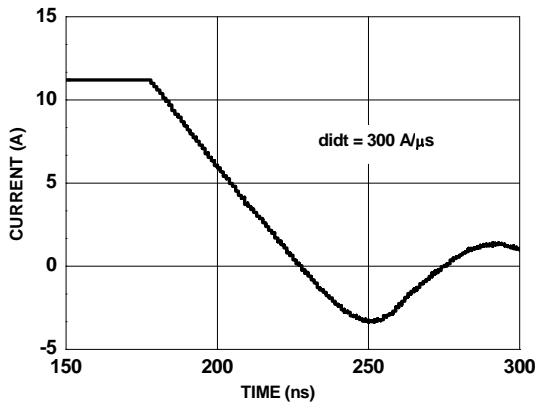


Figure 25. FDMS7600AS SyncFET<sup>™</sup> Body Diode Reverse Recovery Characteristic

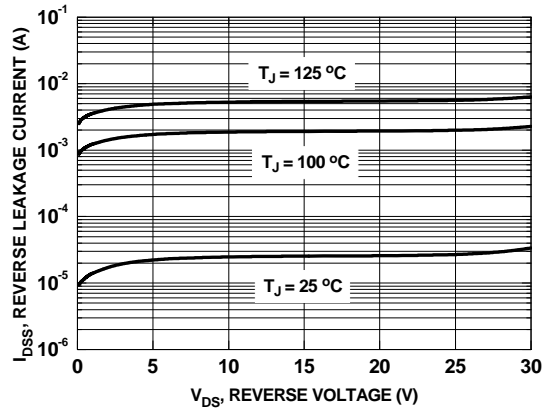
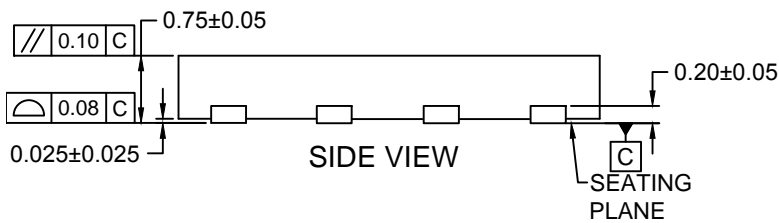
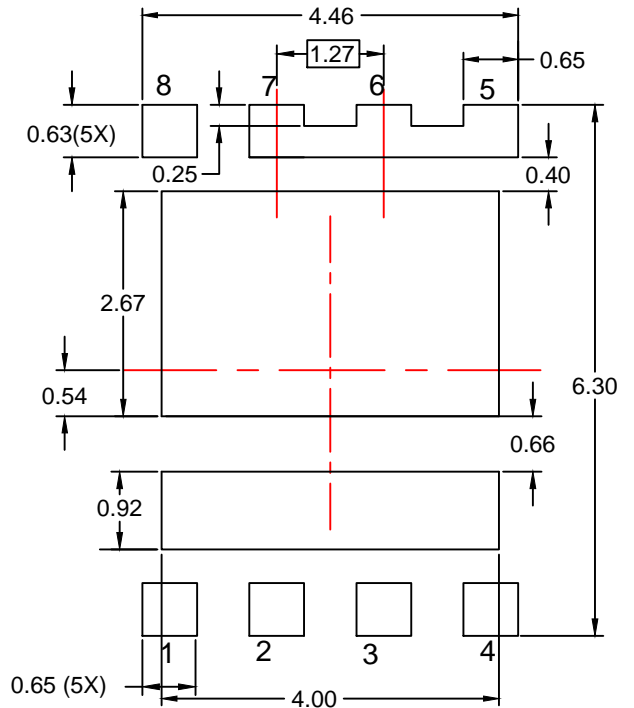
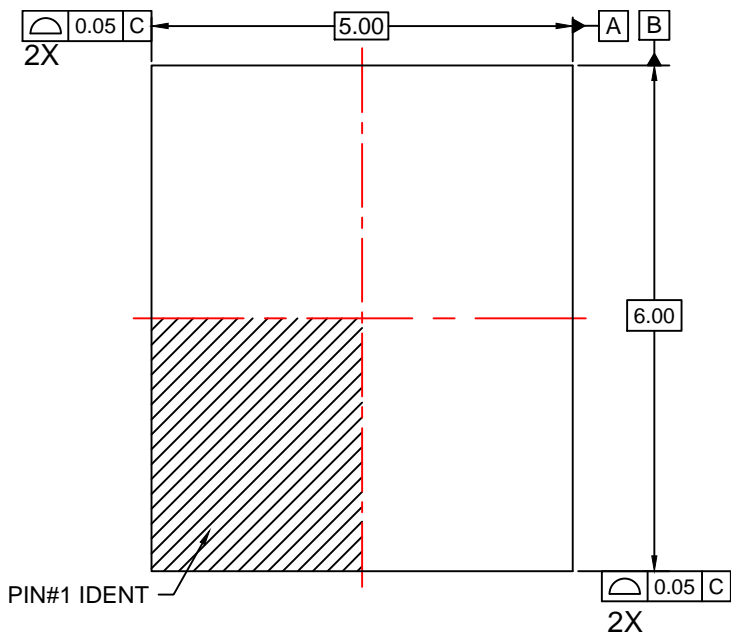
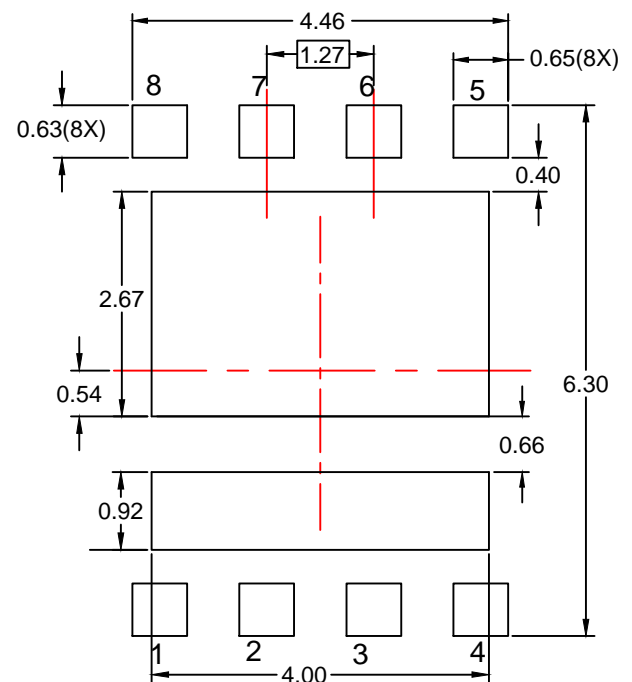
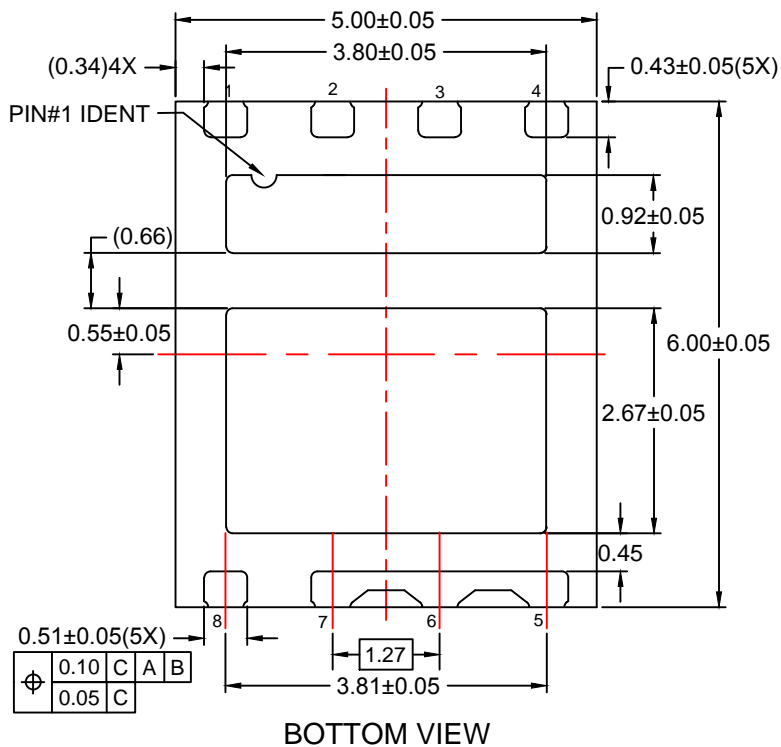


Figure 26. SyncFET<sup>™</sup> Body Diode Reverse Leakage vs. Drain-Source Voltage



RECOMMENDED LAND PATTERN (OPTION 1 - FUSED LEADS 5,6,7)



RECOMMENDED LAND PATTERN (OPTION 2 - ISOLATED LEADS)

**NOTES:**

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC STANDARD.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
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